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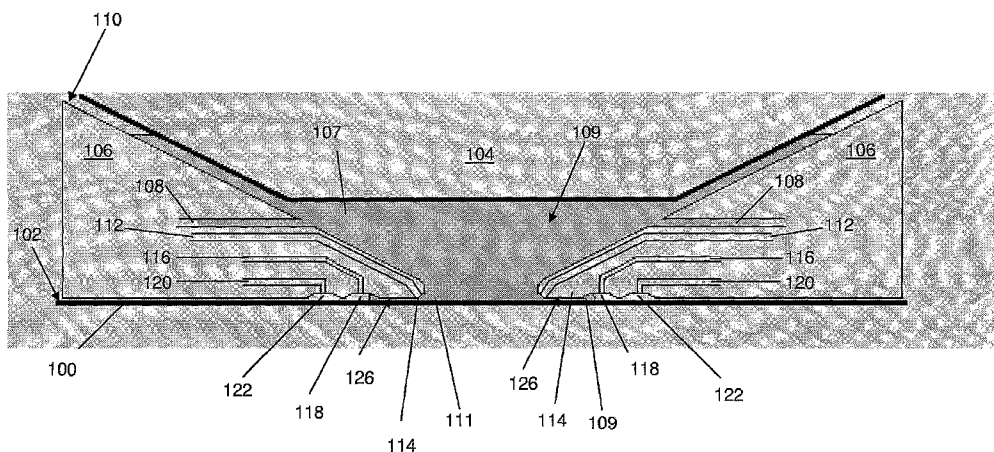
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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: IMMERSION LITHOGRAPHY APPARATUS AND METHOD OF PERFORMING IMMERSION LITHOGRAPHY



(57) Abstract: An immersion lithography apparatus comprises an optical system (104) having a liquid delivery unit (106). The liquid delivery unit (106) is arranged to deliver a layer (111) of an immersion liquid (107) onto a surface (102) of a wafer (100) as well as an annulus of a barrier liquid (200) adjacent an exterior wall of the immersion liquid (107). The presence of the barrier liquid (200) prevents ingress to the immersion liquid (107) of a gas external to the immersion liquid (107).

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IMMERSION LITHOGRAPHY APPARATUS AND METHOD OF PERFORMING  
IMMERSION LITHOGRAPHY

5 **Field of the Invention**

This invention relates to an immersion lithography apparatus of the type, for example, that projects a pattern through an immersion liquid onto a wafer. This invention also relates to a method of performing immersion lithography of the type, for example, that projects a pattern through an immersion liquid onto a wafer.

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**Background of the Invention**

In the field of semiconductor processing, photolithography is a widely employed technique to "pattern", i.e. define a profile in one or more layer of semiconductor material, a semiconductor wafer. Using this technique, hundreds of Integrated Circuits (ICs) formed from an even larger number of transistors can be formed on a wafer of silicon. In this respect, for each wafer, the ICs are formed one at a time and on a layer-by-layer basis.

For about the last four decades, a photolithography apparatus, sometimes known as a cluster or photolithography tool, has been employed to carry out a photolithographic process. The cluster comprises a track unit that prepares the wafer, including providing layers of photosensitive material on the surface of the wafer prior to exposure to a patterned light source. To expose

the wafer to the patterned light source, the wafer is transferred to an optics unit that is also part of the cluster. The patterned light source is generated by passing a beam of light through a chrome-covered mask, the chrome having been patterned with an image of a given layer of an IC to be formed, for example, transistor contacts. Thereafter, the wafer is returned to the track unit for subsequent processing including development of the layers of photosensitive material mentioned above.

10

The wafer, carrying the layers of photosensitive material, is supported by a movable stage. A projection lens focuses the light passing through the mask to form an image on a first field over the layers of photosensitive material where an IC is to be formed, exposing the field of the layers of photosensitive material to the image and hence "recording" the pattern projected through the mask. The image is then projected on another field over the layers of photosensitive material where another IC is to be formed, this field over the layers of photosensitive material being exposed to the projected image, and hence pattern.

The above process is repeated for other fields where other ICs are to be formed. Thereafter, the wafer is, as mentioned above, returned to the track unit, and the exposed layers of photosensitive material, which become soluble or insoluble through exposure depending upon the photosensitive materials used, are developed to leave a "photoresist" pattern corresponding to a negative (or positive) of the image of a layer of one or more ICs to be created. After development, the wafer undergoes various other processes, for example ion implantation, etching or deposition. The remaining layers of

photosensitive material are then removed and fresh layers of photosensitive material are subsequently provided on the surface of the wafer depending upon particular application requirements for patterning another layer of  
5 the one or more ICs to be formed.

In relation to the patterning process, the resolution of a photolithography apparatus, or scanner, impacts upon the width of wires and spaces therebetween that can be  
10 "printed", the resolution being dependent upon the wavelength of the light used and inversely proportional to a so-called "numerical aperture" of the scanner. Consequently, to be able to define very high levels of detail a short wavelength of light is required and/or a  
15 large numerical aperture.

The numerical aperture of the scanner is dependent upon the product of two parameters. A first parameter is the widest angle through which light passing through the lens  
20 can be focused on the wafer, and a second parameter is the refractive index of the medium through which the light passes when exposing the layers of photosensitive material on the wafer.

25 Indeed, to provide the increased resolution demanded by the semiconductor industry, it is known to reduce wavelengths of light used whilst also making lenses bigger to increase the numerical aperture. However, practical limits to the usable wavelengths of light are  
30 currently being reached, for example due to cost of having to use lenses formed from different materials compatible with the lower wavelengths of light, and scarcity of suitable lens materials.

Additionally, the above-described scanner operates in air, air having a refractive index of 1, resulting in the scanner having a numerical aperture between 0 and 1. Since the numerical aperture needs to be as large as possible, and the amount the wavelength of light can be reduced is limited, an improvement to the resolution of the scanner has been proposed that, other than by increasing the size of the lens, uses the scanner in conjunction with a medium having a refractive index greater than that of air, i.e. greater than 1. In this respect, the more recent photolithographic technique proposed, employing water and known as immersion lithography, can achieve higher levels of device integration than can be achieved by air-based photolithography techniques.

Therefore, scanners employing this improvement (immersion scanners) continue to use low wavelengths of light, but the water provides a refractive index of approximately 1.4 at a wavelength of 193 nm between the lens and the wafer, thereby achieving increased depth of focus and effectively increasing the numerical apertures of the immersion lithographic apparatus.

Further, the refractive index of the water is very close to that of quartz from which some lenses are formed, resulting in reduced refraction at the interface between the lens and the water. The reduced refraction allows the size of the lens to be increased, thereby allowing advantage to be taken of the higher available numerical aperture.

However, with the introduction of immersing lithography come technical challenges to be overcome if immersion

lithography is to be a viable lithographic technique for defining sub-45 nm features.

One known immersion lithography apparatus comprises an illumination system to serve as a source of electromagnetic radiation. The illumination system is coupled to a support structure for holding a mask, the support structure being coupled to a first translation apparatus to position the illumination system accurately. A wafer table is disposed beneath the illumination system and is coupled to a second translation apparatus to position accurately the wafer table. A projection system is disposed adjacent the wafer table and projects light from the illumination system onto a wafer located on the wafer table. The projection system comprises an immersion head, which when in use, delivers and maintains an immersion liquid between the immersion head and the wafer.

In operation, the immersion lithography apparatus has a scan mode in which the wafer table is synchronously translated relative to the support structure, the immersion liquid having a leading edge corresponding to a direction of travel of the immersion liquid.

In order to increase wafer yields in connection with photolithographic processing of wafers, it is desirable to increase a velocity of translation of the wafer table relative to the support structure, i.e. to take less time to pattern the wafer. However, as scan rates increase to about  $350 \text{ mms}^{-1}$ , it has been found that the leading edge of the immersion liquid rolls under the immersion liquid causing bubbles to form in the immersion liquid, which are then printed. Indeed, bubbles are known to be a

significant hindrance to successful implementation of the immersion lithography technique. One known solution is to limit the scan rate, but this, of course, impacts negatively upon the achievable wafer yields.

5

Additionally, it is becoming desirable to use so-called "high n", or high refractive index liquids as the immersion liquid. However, high n liquids need to be used in an oxygen-free environment, otherwise the refractive index of the high n begins to change rapidly. Further, due to the relative expense of high n liquids, the high n liquid is likely to be recycled in a closed system.

10

#### **Statement of Invention**

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According to the present invention, there is provided an immersion lithography apparatus and a method of performing immersion lithography as set forth in the appended claims.

20

#### **Brief Description of the Drawings**

At least one embodiment of the invention will now be described, by way of example only, with reference to the accompanying drawings, in which:

25

FIG. 1 is a schematic diagram of a liquid delivery unit of an immersion lithography apparatus constituting an embodiment of the invention;

30

FIG. 2 is a schematic diagram of a part of the liquid delivery unit of FIG. 1, but in greater detail.

### Description of Preferred Embodiments

Throughout the following description identical reference  
5 numerals will be used to identify like parts.

Referring to FIG. 1, a semiconductor wafer 100 having  
layers of photosensitive material disposed thereon (not  
shown in FIG. 1), the layers of photosensitive material  
10 having an upper surface 102, is disposed upon a substrate  
stage (not shown) of an immersion lithography apparatus  
arranged to carry the wafer 100. In this example, the  
immersion lithography apparatus is a modified TWINSCAN™  
XT:1250i lithography scanner available from ASML. The  
15 lithography scanner is a complex apparatus having many  
parts, the structure and operation of which, are not  
directly relevant to the embodiments disclosed herein.  
Consequently, for the sake of clarity and conciseness of  
description, only the parts of the lithography scanner of  
20 particular relevance to the embodiment described herein  
will be described.

The immersion lithography apparatus comprises an optical  
exposure (projection or catadioptric) system 104  
25 connected to a liquid delivery unit 106, sometimes known  
as a "showerhead". A so-called immersion liquid 107 is  
disposed between the bottom of the optical exposure  
system 104 and the surface 102 of the layers of  
photosensitive material.

30

The liquid delivery unit 106 comprises immersion liquid  
inlet/outlet ports 108 in fluid communication with a  
reservoir 109 defined by an inner peripheral surface 110  
of the liquid delivery unit 106 and the upper surface



102. A source of a barrier liquid 112 is coupled to barrier liquid inlet/outlet ports 114. A vacuum pump (not shown) is coupled to vacuum ports 116, the vacuum ports 116 being in fluid communication with a first channel loop 118. A compressor (not shown) is coupled to air supply ports 120, the air supply ports 120 being in fluid communication with a second channel loop 122.

In operation, a quantity of an immersion liquid 107 is delivered to the reservoir 109 via the immersion liquid inlet/outlet ports 108, a layer 111 of the immersion liquid 107 lying between the surface 102 and the liquid delivery unit 106. The immersion liquid 107 is a high refractive index (high-n) liquid having a refractive index between about 1.5 and about 1.8, i.e. greater than the refractive index of water, for example between about 1.6 and 1.7. In this example, the immersion liquid 107 is Dupont® IF132 having a refractive index of close to 1.65. However, the skilled person will appreciate that liquids having a lower refractive index, for example water, can be used.

Turning to FIG. 2, a quantity of the barrier liquid 200 is deposited adjacent the layer 111 of the immersion liquid 107 as an annulus, in this example, to surround the layer 111 of the immersion liquid 107 and "cap" the layer 111 of the immersion liquid 107. The barrier liquid 200 is, in this example, an aqueous-based liquid. However, the skilled person will appreciate that the barrier liquid 200 can be non-aqueous-based. The barrier liquid 200 has a density of a value so that the barrier liquid 200 does not mix with the immersion liquid 107 during translation of the wafer 100 relative to the liquid delivery unit 106. The density of the barrier

liquid 200 can be greater than that of the immersion liquid 107. The density of the barrier liquid 200 can be between about  $700 \text{ kgm}^{-3}$  and about  $1600 \text{ kgm}^{-3}$ , for example oil or dodecane. The density of the barrier liquid 200 can be between about  $800 \text{ kgm}^{-3}$  and about  $1500 \text{ kgm}^{-3}$ . In this example, the barrier liquid 200 is dodecane and has a density of about  $750 \text{ kgm}^{-3}$  at  $25 \text{ }^\circ\text{C}$ . In this example, the barrier liquid 200 is also hydrophobic, though the skilled person will appreciate that hydrophilic liquids can be used.

The optical exposure system 104 coupled to the liquid delivery unit 106 scans the surface 102 of the layers of photosensitive material 202 by translation of the wafer beneath the optical exposure system 104 in order to project a pattern onto the layers of photosensitive material 202 in a manner known for the lithography scanner. A vacuum provided to the first channel loop 114 via the vacuum ports 112 and pressurised air expelled into the second channel loop 118 via the air supply ports 116 prevent egress of the immersion liquid 107 and the barrier liquid 200 through a clearance 126 between the liquid delivery unit 106 and the surface 102, thereby serving as a seal and a means of preventing spurious deposition of the immersion liquid 107 and the barrier liquid 200 on the surface 102.

Whilst the layer 111 of the immersion liquid 107 moves relative to the surface 102 of the wafer 100, a first exterior edge or front 204 of the layer 111 of the immersion liquid 107 "rolls" in a direction of travel of the layer 111 of the immersion liquid 107 relative to the surface 102 of the wafer 100. The annular quantity of the barrier liquid 200 also moves relative to the surface 102

of the wafer 100 with the layer 111 of the immersion liquid 107. Independently of the first exterior surface 204, a second exterior edge or front 206 of the barrier liquid 200 also rolls in the direction of travel of the  
5 layer 111 of the immersion liquid 107 relative to the surface 102 of the wafer 100.

As a result of the presence of the barrier liquid 200 surrounding the layer 111 of the immersion liquid 107,  
10 the immersion liquid 107 is isolated from environmental gases, for example oxygen, that are usually present in an atmosphere in which the scanner is disposed. Additionally, the provision of the barrier liquid 200 also prevents the layer 111 of the immersion liquid 107  
15 from enveloping quantities of the environmental gases.

It is thus possible to provide an immersion lithography apparatus and a method of performing immersion lithography that prevents absorption of oxygen by the  
20 immersion liquid. Additionally, the formation of bubbles in the immersion liquid is mitigated at elevated scanning rates, for example above  $500 \text{ mms}^{-1}$ . Of course, the above advantages are exemplary, and these or other advantages may be achieved by the invention. Further, the skilled  
25 person will appreciate that not all advantages stated above are necessarily achieved by embodiments described herein.

It should be appreciated that quoted refractive indices  
30 herein are quoted with respect to a given wavelength of electromagnetic radiation, for example 193 nm.

**Claims (PCT)**

1. An immersion lithography apparatus comprising:  
an optical system (104) for projecting a pattern  
5 onto a part of a surface (102) of a wafer (100), the  
optical system (104) having a liquid delivery unit (106)  
arranged to dispose, when in use, a quantity of an  
immersion liquid (107) for filling a space (111) between  
10 the optical system (104) and the surface of the wafer  
(100);  
a carrier unit for carrying the wafer (100), the  
carrier unit being arranged to move, when in use,  
relative to the optical system (104) for exposing  
different parts of the surface of the wafer (100) to the  
15 pattern; characterised by:  
a source (114) of a barrier liquid (200) arranged to  
provide, when in use, a quantity of the barrier liquid  
(200) adjacent the quantity of the immersion liquid  
(107), thereby preventing ingress to the quantity of the  
20 immersion liquid (107) of a gas external to the quantity  
of the barrier liquid (200).
2. An apparatus as claimed in Claim 1, wherein the  
quantity of the immersion liquid (107) has a leading edge  
25 (204) when the carrier unit moves relative to the optical  
system (104), the quantity of the barrier liquid (200)  
being disposed adjacent the leading edge (204) of the  
quantity of the immersion liquid (107).
- 30 3. An apparatus as claimed in Claim 1 or Claim 2,  
wherein the refractive index of the immersion liquid  
(107) is between about 1.5 and about 1.8.

4. An apparatus as claimed in Claim 1 or Claim 2 or Claim 3, wherein the refractive index of the immersion liquid (107) is between about 1.6 and about 1.7.

5

5. An apparatus as claimed in any one of the preceding claims, wherein a density of the barrier liquid (200) is of a value so that, when in use, the barrier liquid (200) does not mix with the immersion liquid (107) during the relative movement of the carrier unit.

6. An apparatus as claimed in Claim 5, wherein the density of the barrier liquid (200) is between about 700  $\text{kgm}^{-3}$  and about 1600  $\text{kgm}^{-3}$ .

15

7. An apparatus as claimed in Claim 5 or Claim 6, wherein the density of the barrier liquid (200) is between about 800  $\text{kgm}^{-3}$  and about 1500  $\text{kgm}^{-3}$ .

8. An apparatus as claimed in any one of the preceding claims, wherein the immersion liquid (107) rolls, when in use, and the quantity of barrier liquid (200) prevents envelopment of the gas by the quantity of the immersion liquid (107) as the immersion liquid (107) rolls.

25

9. An apparatus as claimed in any one of the preceding claims, wherein the barrier liquid (200) is aqueous.

10. An apparatus as claimed in any one of Claims 1 to 8, wherein the barrier liquid (200) is non-aqueous.

30

11. An apparatus as claimed in any one of the preceding claims, wherein the barrier liquid (200) is hydrophobic.

12. An apparatus as claimed in any one of the preceding claims, wherein the fluid delivery unit (106) comprises:

a first port (108) for deploying the quantity of the immersion liquid (107); and

5 a second port (114) for deploying the quantity of the barrier liquid (200).

13. A method of performing immersion lithography, the method comprising the steps of:

10 disposing a quantity of an immersion liquid (107) to fill a space (126) between an optical system (104) of an immersion lithography apparatus and a surface (102) of a wafer (100);

projecting a pattern onto a part of the surface (102) of the wafer (100);

moving the wafer (100) relative to the optical system (104) for exposing different parts of the surface (102) of the wafer (100) to the pattern; the method characterised by:

20 providing a quantity of a barrier liquid (200) adjacent the quantity of the immersion liquid (107), thereby preventing ingress to the quantity of the immersion liquid (107) of a gas external to the quantity of the barrier liquid (200).

25

**AMENDED CLAIMS**

received by the International Bureau on 24 July 2006 (24.07.2006)  
+STATEMENT

**Claims (PCT)**

1. An immersion lithography apparatus comprising:

an optical system (104) for projecting a pattern  
5 onto a part of a surface (102) of a wafer (100), the  
optical system (104) having a liquid delivery unit (106)  
arranged to dispose, when in use, a quantity of an  
immersion liquid (107) for filling a space (111) between  
the optical system (104) and the surface of the wafer  
10 (100);

a carrier unit for carrying the wafer (100), the  
carrier unit being arranged to move, when in use,  
relative to the optical system (104) for exposing  
different parts of the surface of the wafer (100) to the  
15 pattern; characterised by:

a source (114) of a barrier liquid (200) arranged to  
provide, when in use, a quantity of the barrier liquid  
(200) adjacent and in contact with the quantity of the  
immersion liquid (107), thereby preventing ingress to the  
20 quantity of the immersion liquid (107) of a gas external  
to the quantity of the barrier liquid (200).

2. An apparatus as claimed in Claim 1, wherein the  
quantity of the immersion liquid (107) has a leading edge  
25 (204) when the carrier unit moves relative to the optical  
system (104), the quantity of the barrier liquid (200)  
being disposed adjacent the leading edge (204) of the  
quantity of the immersion liquid (107).

30 3. An apparatus as claimed in Claim 1 or Claim 2,  
wherein the refractive index of the immersion liquid  
(107) is between about 1.5 and about 1.8.

12. An apparatus as claimed in any one of the preceding claims, wherein the fluid delivery unit (106) comprises:

a first port (108) for deploying the quantity of the immersion liquid (107); and

5 a second port (114) for deploying the quantity of the barrier liquid (200).

13. A method of performing immersion lithography, the method comprising the steps of:

10 disposing a quantity of an immersion liquid (107) to fill a space (126) between an optical system (104) of an immersion lithography apparatus and a surface (102) of a wafer (100);

projecting a pattern onto a part of the surface  
15 (102) of the wafer (100);

moving the wafer (100) relative to the optical system (104) for exposing different parts of the surface (102) of the wafer (100) to the pattern; the method characterised by:

20 providing a quantity of a barrier liquid (200) adjacent and in contact with the quantity of the immersion liquid (107), thereby preventing ingress to the quantity of the immersion liquid (107) of a gas external to the quantity of the barrier liquid (200).

25



**Statement under Article 19(1) PCT**

**Re: Patent Application PCT/EP2005/014216 in the name of Freescale Semiconductor, Inc.**

**Amendments and support therefor:**

- (i) Original Claim 1 has been amended at line 18 to recite that the quantity of barrier liquid is adjacent and in contact with the quantity of immersion liquid. Basis for this additional wording can be found in FIG. 2 of the drawings;
- (ii) Original Claim 13 has also been amended (at line 21) to recite that the quantity of barrier liquid is adjacent and in contact with the quantity of immersion liquid. Basis for this amendment is, of course, the same.

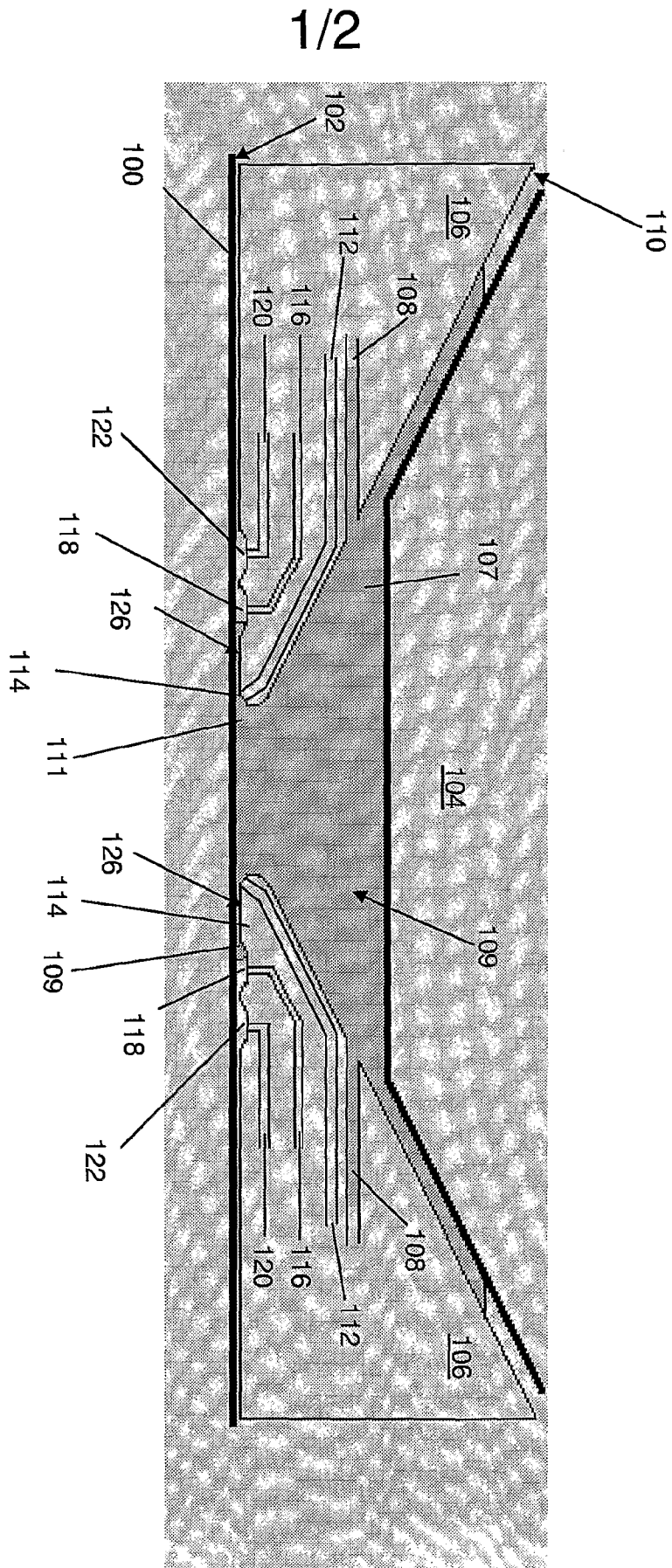


FIG. 1

2/2

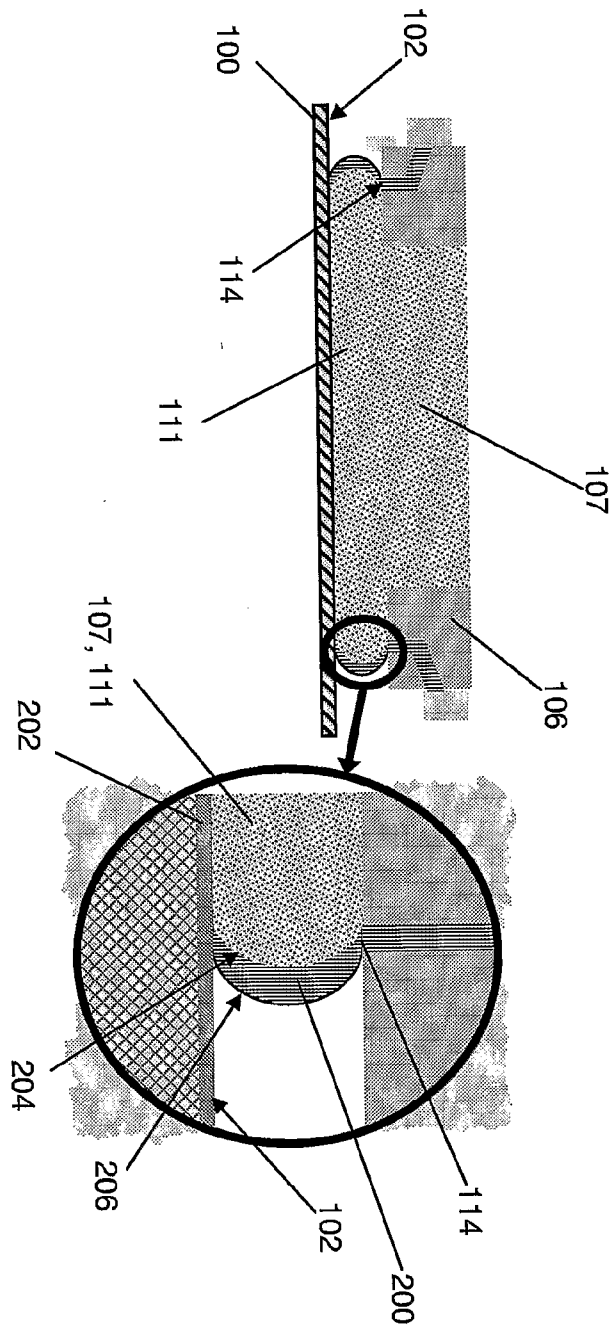


FIG. 2

# INTERNATIONAL SEARCH REPORT

International application No  
PCT/EP2005/014216

**A. CLASSIFICATION OF SUBJECT MATTER**  
INV. G03F7/20

According to International Patent Classification (IPC) or to both national classification and IPC

**B. FIELDS SEARCHED**

Minimum documentation searched (classification system followed by classification symbols)  
G03F

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	EP 1 494 079 A (ASML NETHERLANDS B.V) 5 January 2005 (2005-01-05)	1,2, 8-10,12, 13
Y	paragraph [0010] - paragraph [0011] paragraph [0053] - paragraph [0066]; figure 4	3,4,6,7
X	----- US 2005/122505 A1 (MIYAJIMA YOSHIKAZU) 9 June 2005 (2005-06-09)	1,2,5, 10,12,13
Y	paragraph [0049] - paragraph [0057]; figures 4-6	6,7,11
Y	----- EP 1 571 698 A (NIKON CORPORATION) 7 September 2005 (2005-09-07) paragraph [0004]	3,4
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Further documents are listed in the continuation of Box C.

See patent family annex.

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- \*X\* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
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- \*&\* document member of the same patent family

Date of the actual completion of the international search

11 May 2006

Date of mailing of the international search report

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Name and mailing address of the ISA/

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van Toledo, W

INTERNATIONAL SEARCH REPORT

International application No  
PCT/EP2005/014216

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 2003/107184 A1 (PLATNER DAVID K) 12 June 2003 (2003-06-12) paragraph [0023] -----	11
Y	US 2004/038060 A1 (KAWAKAMI NOBUYUKI ET AL) 26 February 2004 (2004-02-26) paragraph [0022] - paragraph [0024] -----	11

# INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No  
PCT/EP2005/014216

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